
2SK3001

GaAs HEMT
Low Noise Amplifier

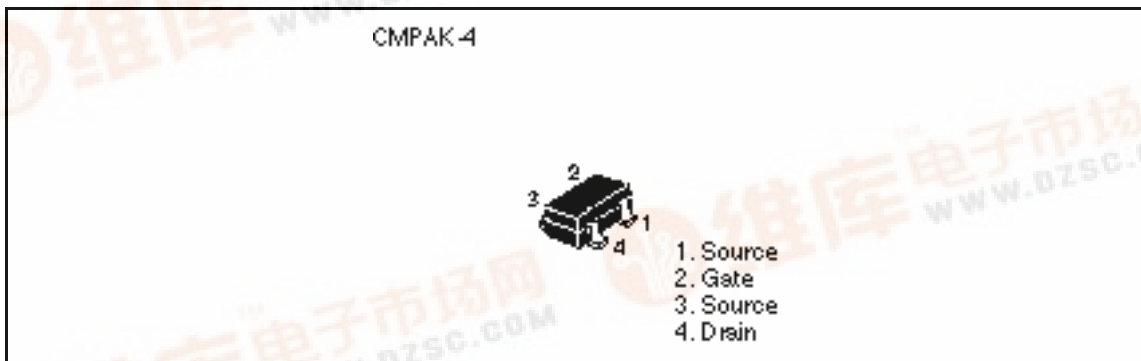
HITACHI

ADE-208-597(Z)
1st. Edition
December 1997

Features

- Excellent low noise characteristics.
Fmin = 0.8 dB typ. (3 V, 5 mA, 0.9 GHz)
- High associated gain.
Ga = 18 dB typ. (3 V, 5 mA, 0.9 GHz)
- Small package. (CMPAK-4)

Outline



This document may, wholly or partially, be subject to change without notice.

This Device is sensitive to Electro Static Discharge.
It is recommended to adopt appropriate cautions when handling this transistor.

CAUTION

This product use GaAs. Since dust or fume of GaAs is highly poisonous to human body, please do not treat them mechanically in the manner which might expose to the Air. And it should never be thrown out with general industrial or domestic wastes.

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Absolute Maximum Ratings (Ta = 25°C)

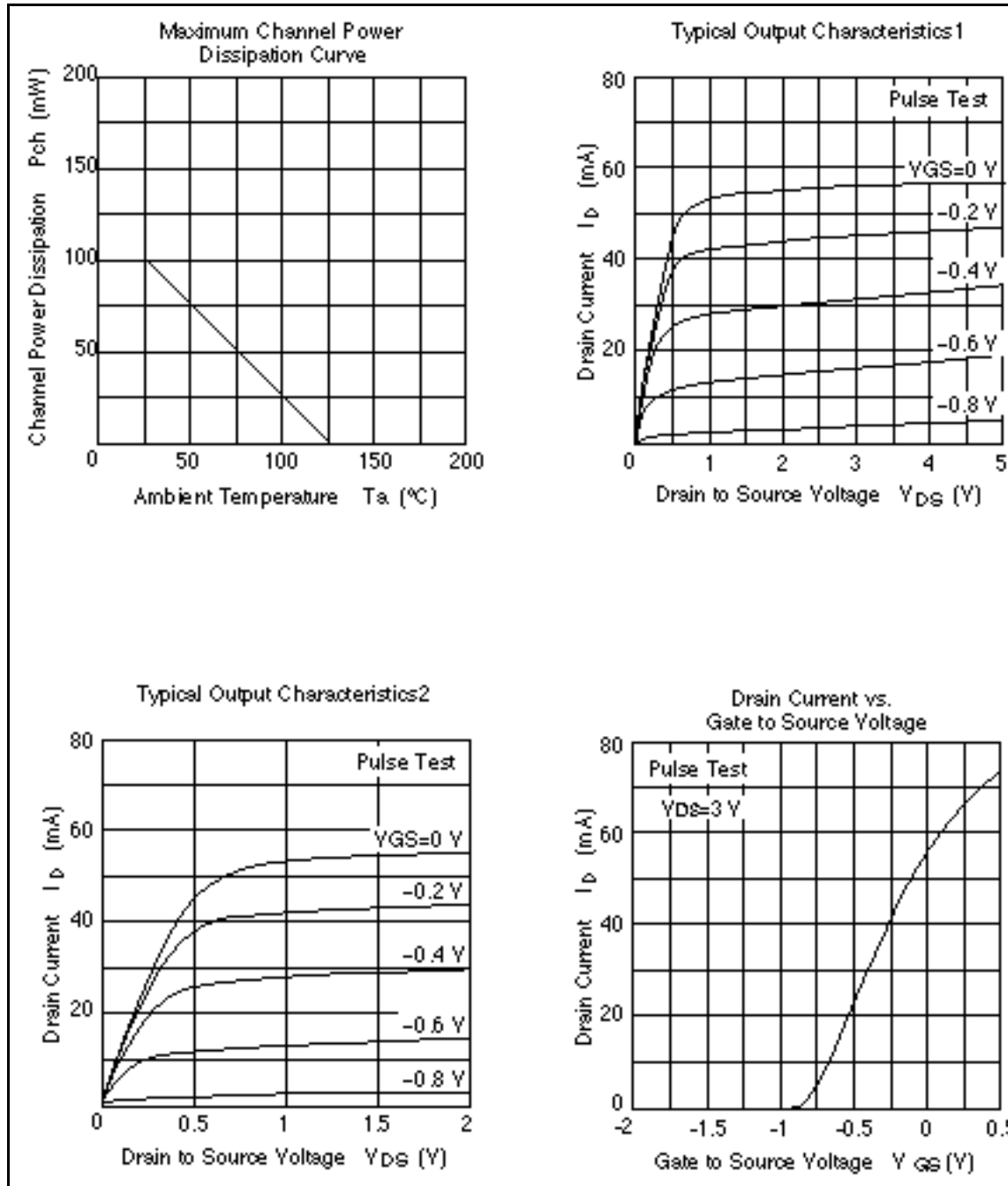
Item	Symbol	Ratings	Unit
Drain to source voltage	V_{DSS}	6	V
Gate to source voltage	V_{GSO}	-4	V
Gate to drain voltage	V_{GDO}	-4	V
Drain current	I_D	20	mA
Channel dissipation	Pch	100	mW
Channel temperature	Tch	125	°C
Storage temperature	Tstg	-55 to +125	°C

Electrical Characteristics (Ta = 25°C)

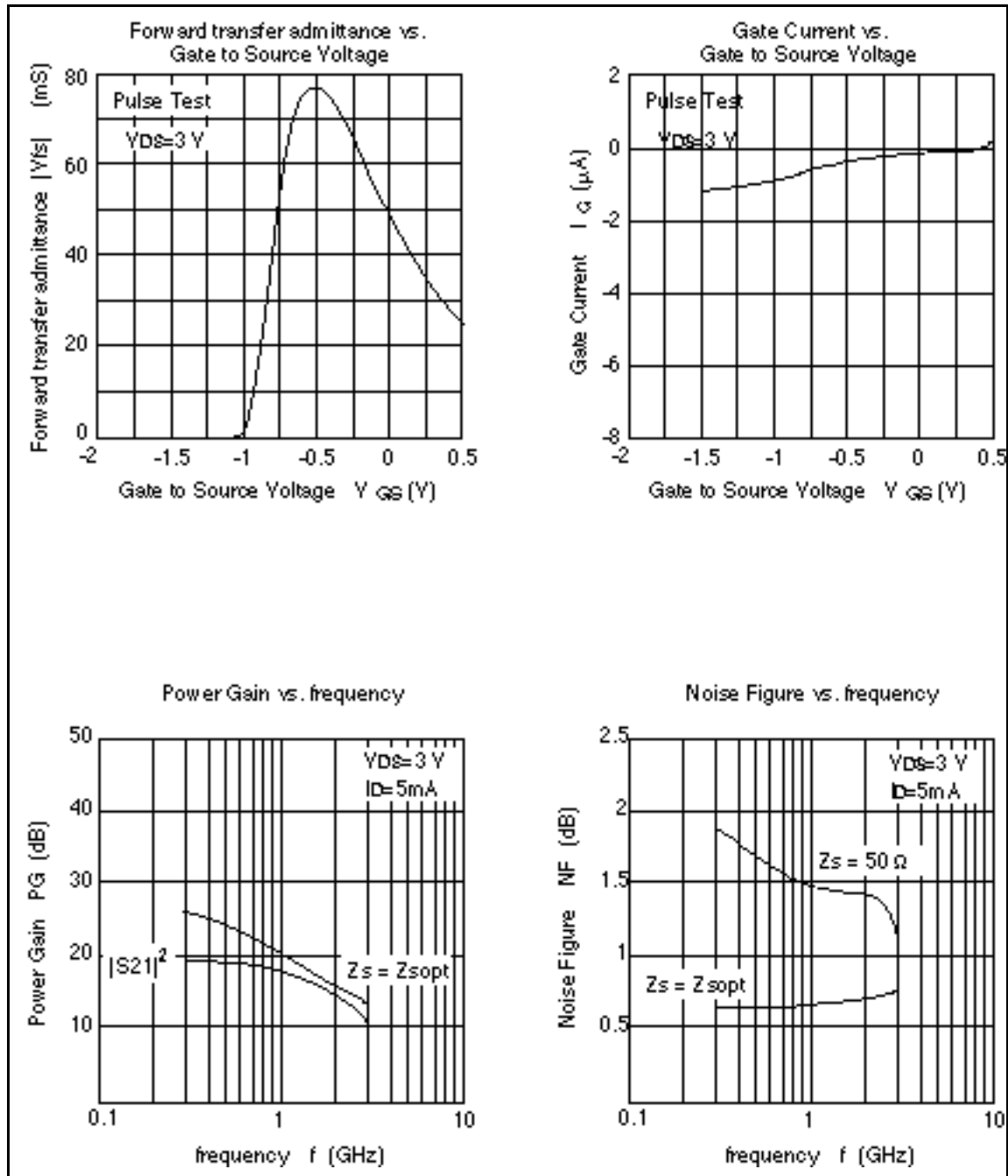
Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Gate to source leak current	I_{GSS}	—	—	-20	μA	$V_{GS} = -4\text{ V}, V_{DS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	-0.5	—	-1.5	V	$V_{DS} = 3\text{ V}, I_D = 100\text{ μA}$
Drain to source current	I_{DSS}	35	50	70	mA	$V_{DS} = 3\text{ V}, V_{GS} = 0$ Pulse test
Forward transfer admittance	$ y_{fs} $	40	60	—	mS	$V_{DS} = 3\text{ V}, I_D = 10\text{ mA}$ $f = 1\text{ kHz}$
Power Gain	PG	15.0	18.0	—	dB	$V_{DS} = 3\text{ V}, I_D = 5\text{ mA}$ $f = 0.9\text{ GHz}$
Noise Figure	NF	—	0.8	1.2	dB	
Associated gain	Ga	—	21.0	—	dB	$V_{DS} = 3\text{ V}, I_D = 5\text{ mA}$ $f = 0.8\text{ GHz}, Z_s = Z_{sopt}$
Minimum noise figure	Fmin	—	0.7	—	dB	
Associated gain	Ga	—	16.0	—	dB	$V_{DS} = 3\text{ V}, I_D = 5\text{ mA}$ $f = 1.8\text{ GHz}, Z_s = Z_{sopt}$
Minimum noise figure	Fmin	—	0.75	—	dB	

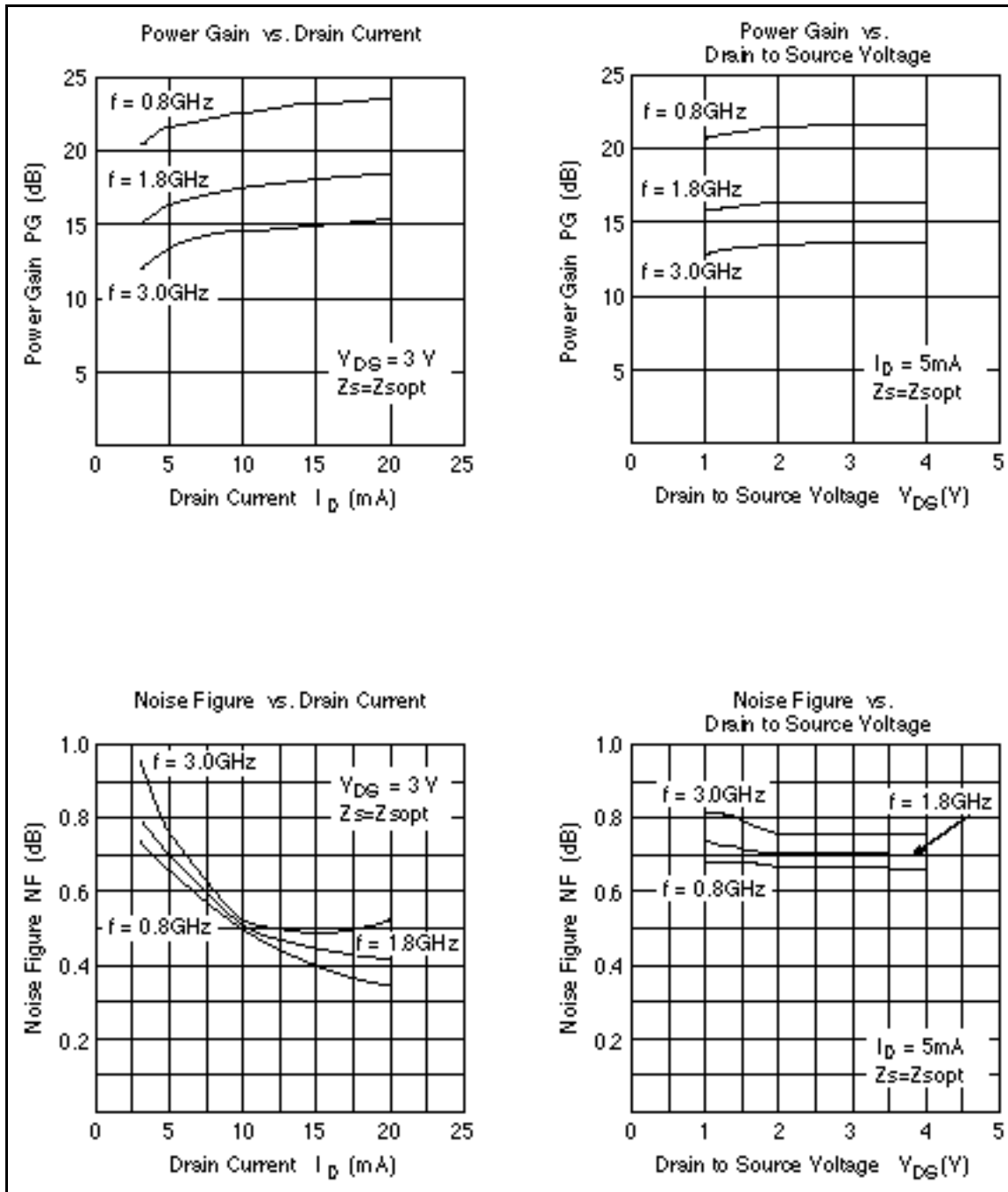
Note: Marking of 2SK3001 is "YX—"

Main Characteristics



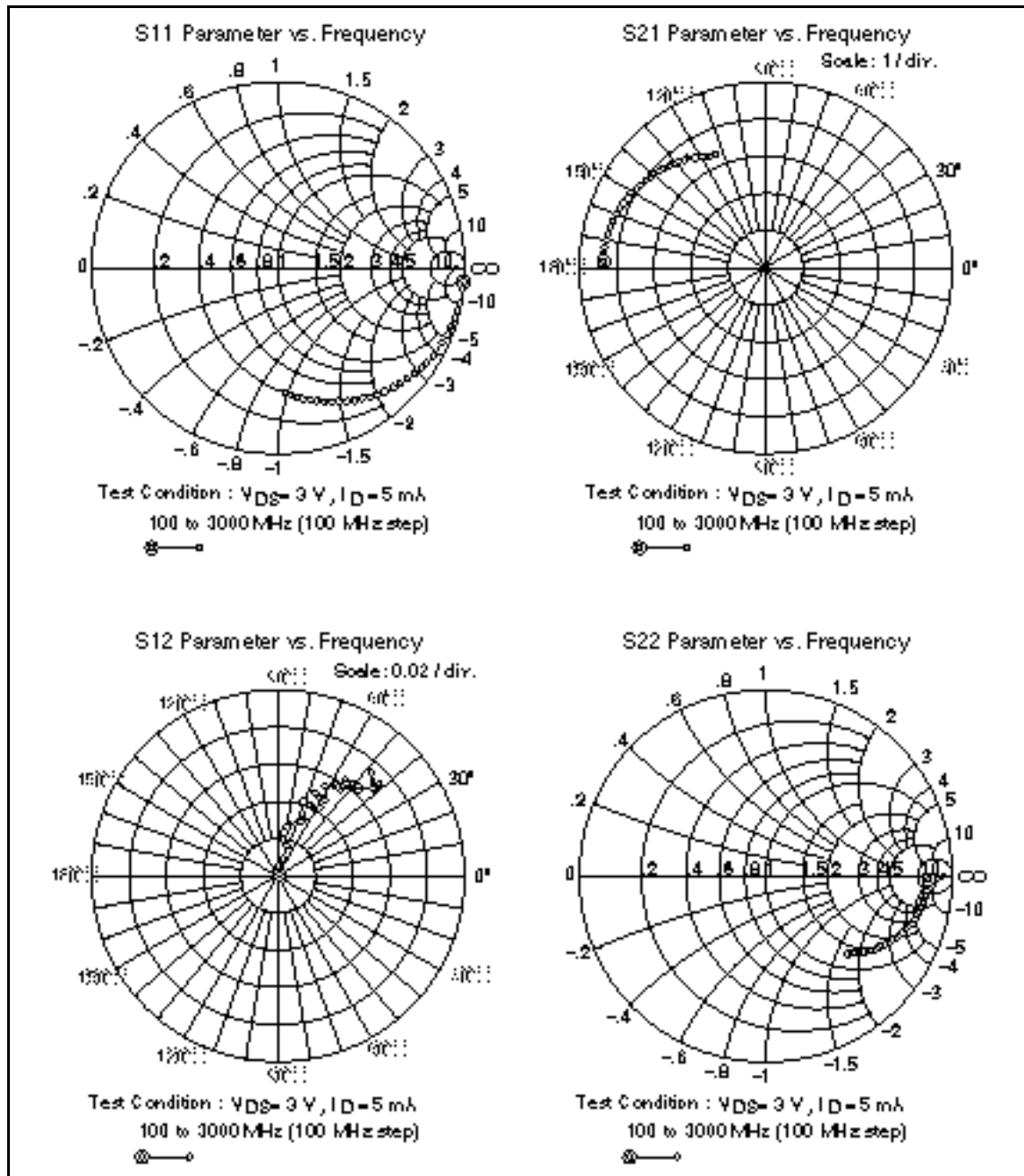
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Sparameter (Smith Plot $Z_0=50\Omega$)

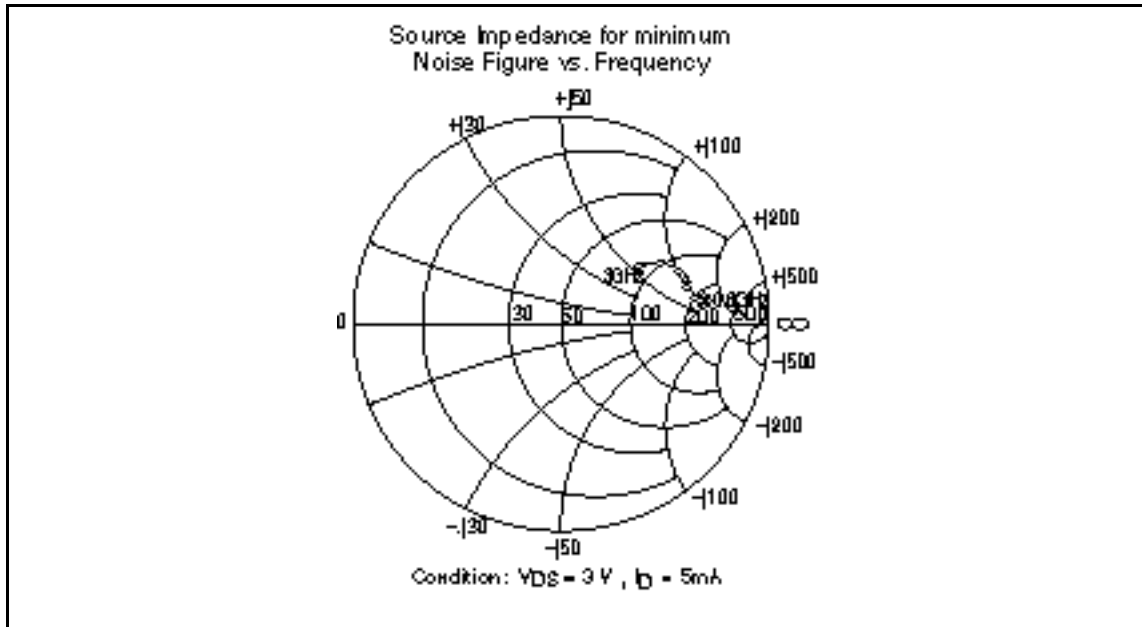


Sparameter ($V_{DS} = 3 \text{ V}$, $I_D = 5 \text{ mA}$, $Z_o = 50 \text{ } \Omega$)

Freq (GHz)	S11 (Mag)	S11 (Ang)	S21 (Mag)	S21 (Ang)	S12 (Mag)	S12 (Ang)	S22 (Mag)	S22 (Ang)
0.1	0.998	-4.1	4.4	177.6	0.001	49.2	0.875	-1.2
0.2	0.995	-6.5	4.4	175.1	0.005	86.3	0.869	-3.1
0.3	0.993	-10.9	4.4	172.6	0.010	75.2	0.869	-5.1
0.4	0.990	-13.4	4.3	170.2	0.017	73.6	0.863	-6.7
0.5	0.989	-14.5	4.3	169.1	0.015	82.9	0.865	-7.1
0.6	0.981	-17.0	4.3	166.3	0.020	81.6	0.859	-9.0
0.7	0.976	-20.0	4.3	163.9	0.026	73.7	0.856	-10.6
0.8	0.965	-23.5	4.3	161.4	0.025	74.3	0.851	-12.1
0.9	0.956	-28.2	4.2	159.0	0.032	76.5	0.834	-14.0
1.0	0.949	-31.1	4.2	156.4	0.029	75.2	0.837	-15.4
1.1	0.942	-33.9	4.2	154.3	0.036	65.0	0.830	-16.8
1.2	0.930	-36.3	4.1	152.0	0.039	67.0	0.819	-18.4
1.3	0.918	-39.5	4.1	149.6	0.037	65.4	0.810	-20.1
1.4	0.903	-42.2	4.0	147.4	0.042	61.2	0.800	-21.8
1.5	0.895	-44.8	4.0	145.1	0.045	65.9	0.789	-23.1
1.6	0.882	-47.8	3.9	143.1	0.046	60.5	0.779	-24.4
1.7	0.869	-50.9	4.0	140.7	0.053	61.8	0.768	-26.0
1.8	0.856	-53.3	3.9	138.3	0.056	57.4	0.753	-27.2
1.9	0.843	-55.6	3.8	136.7	0.055	56.8	0.747	-28.7
2.0	0.826	-59.0	3.9	133.9	0.059	53.8	0.736	-30.4
2.1	0.814	-61.8	3.8	132.3	0.059	52.9	0.720	-31.5
2.2	0.800	-64.0	3.7	130.0	0.062	48.2	0.710	-32.6
2.3	0.785	-67.0	3.7	128.1	0.059	51.5	0.700	-34.4
2.4	0.767	-69.8	3.6	126.8	0.063	48.5	0.692	-35.4
2.5	0.751	-72.4	3.6	123.5	0.065	47.6	0.676	-36.7
2.6	0.742	-75.0	3.5	123.3	0.065	47.4	0.661	-37.9
2.7	0.719	-78.3	3.5	120.0	0.063	48.7	0.652	-39.2
2.8	0.710	-80.3	3.4	118.9	0.074	46.7	0.645	-40.0
2.9	0.689	-82.8	3.3	116.9	0.070	41.0	0.630	-41.4
3.0	0.675	-85.6	3.4	116.0	0.074	41.8	0.618	-43.7

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optimize ($V_{DS} = 3\text{ V}$, $I_D = 5\text{ mA}$)

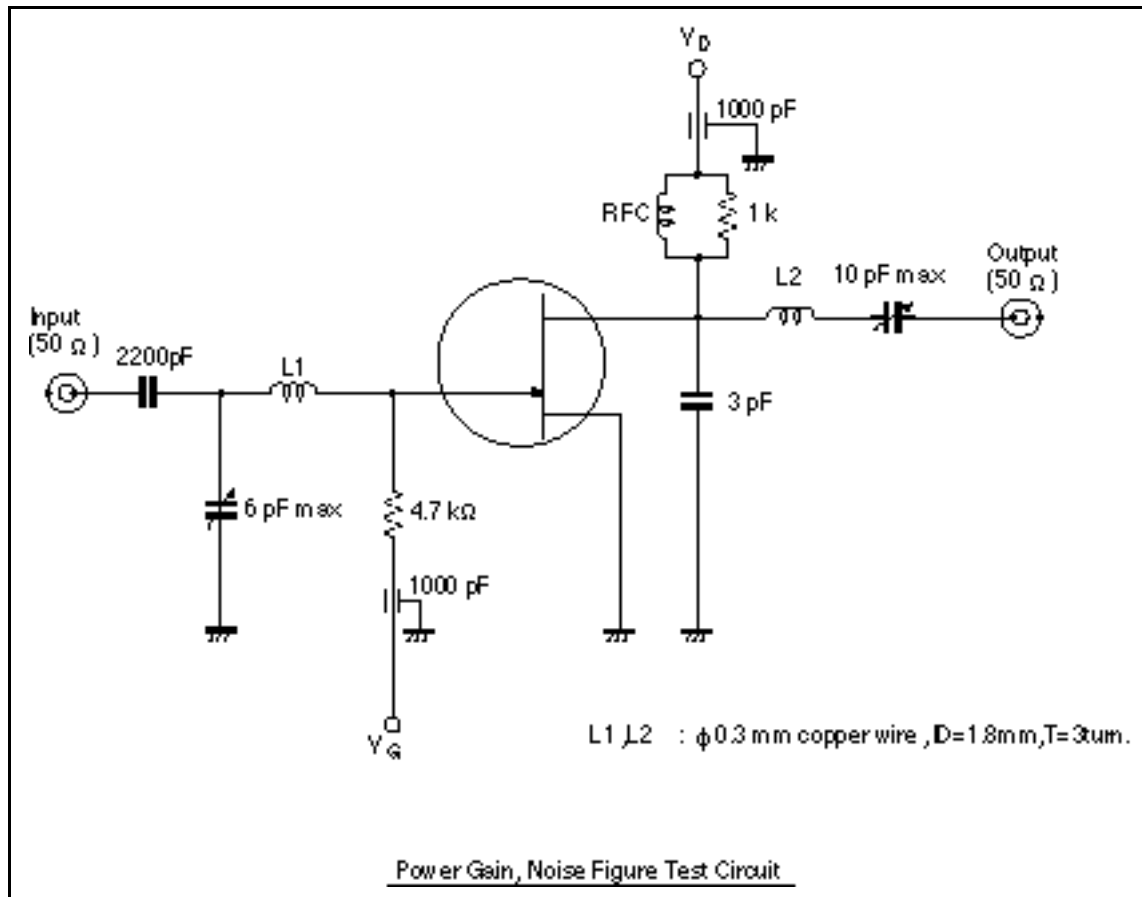


Noise parameter ($V_{DS} = 3\text{ V}$, $I_D = 5\text{ mA}$)

Freq (GHz)	Fmin ¹ (dB)	Ga (dB)	Gopt (Mag)	Gopt (Ang)	RN ()	NF 50 ² (dB)	S21 ² (dB)	S21 ² -
0.8	0.67	21.7	0.69	8.8	19.1	1.53	18.2	4.26
0.9	0.67	21.0	0.68	9.8	18.7	1.50	18.0	4.24
1.0	0.67	20.3	0.66	10.7	18.4	1.48	17.5	4.19
1.5	0.69	17.6	0.64	15.7	17.5	1.44	16.0	3.99
1.7	0.70	16.8	0.64	17.8	17.4	1.44	15.3	3.92
1.8	0.71	16.4	0.64	18.9	17.3	1.44	15.0	3.88
1.9	0.71	16.1	0.64	20.1	17.1	1.44	14.8	3.85
2.0	0.72	15.8	0.64	21.3	17.0	1.44	14.2	3.76
2.2	0.72	15.2	0.63	23.8	16.6	1.43	13.6	3.69
2.5	0.74	14.6	0.60	28.1	15.6	1.37	12.3	3.50
2.7	0.74	14.2	0.56	31.3	14.6	1.30	11.9	3.44
3.0	0.76	13.6	0.47	36.7	12.6	1.15	11.1	3.33

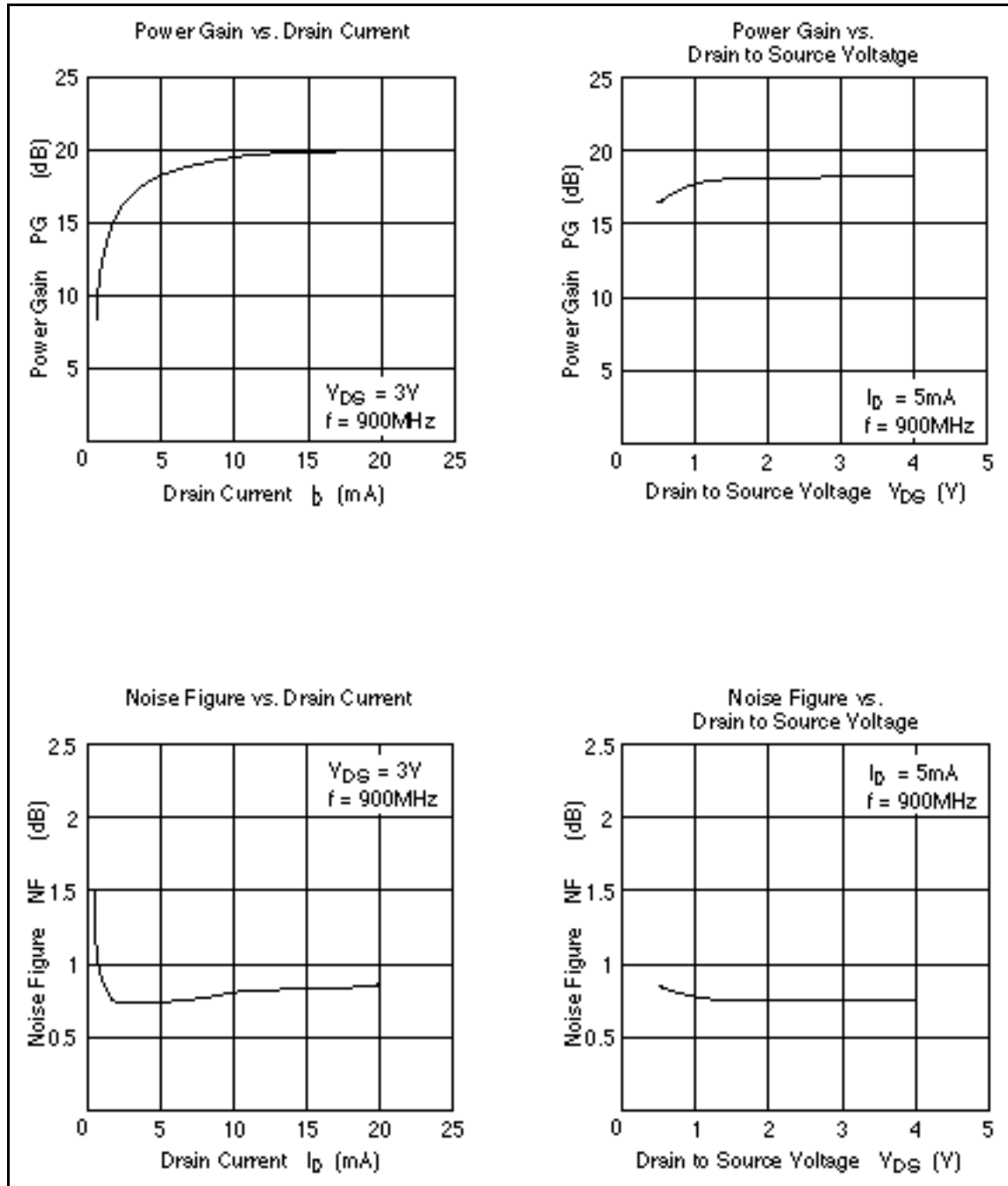
note 1. Input matched for minimum noise figure, Output for maximum gain.

2. $Z_s = Z_L = 50$

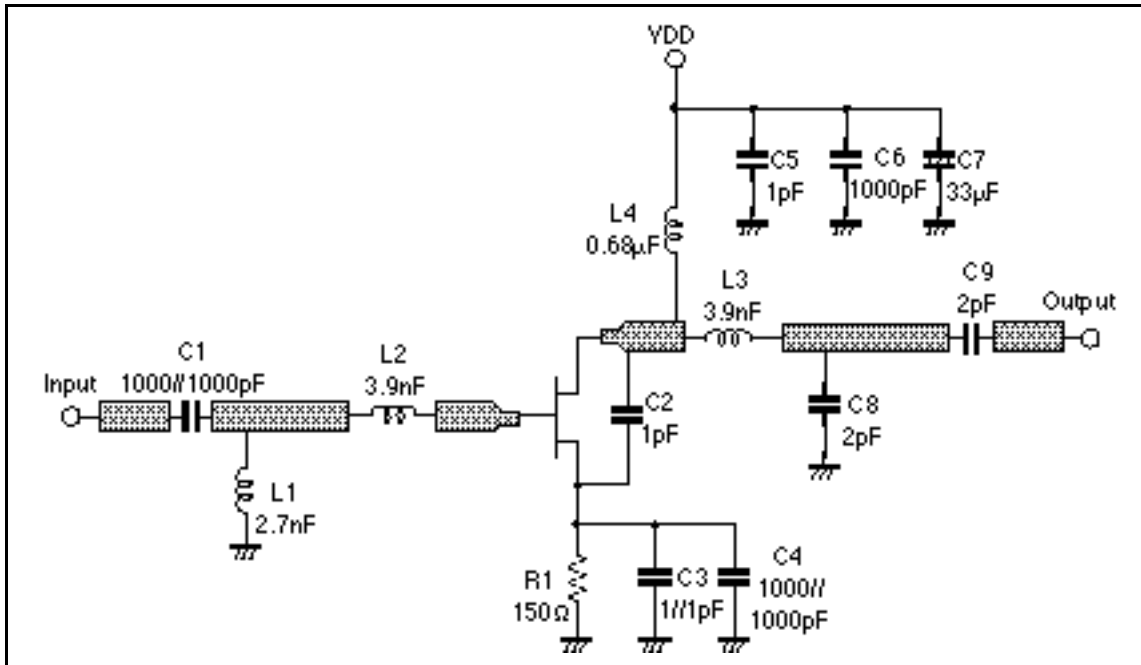
Test Fixture ($f = 0.9 \text{ GHz}$)

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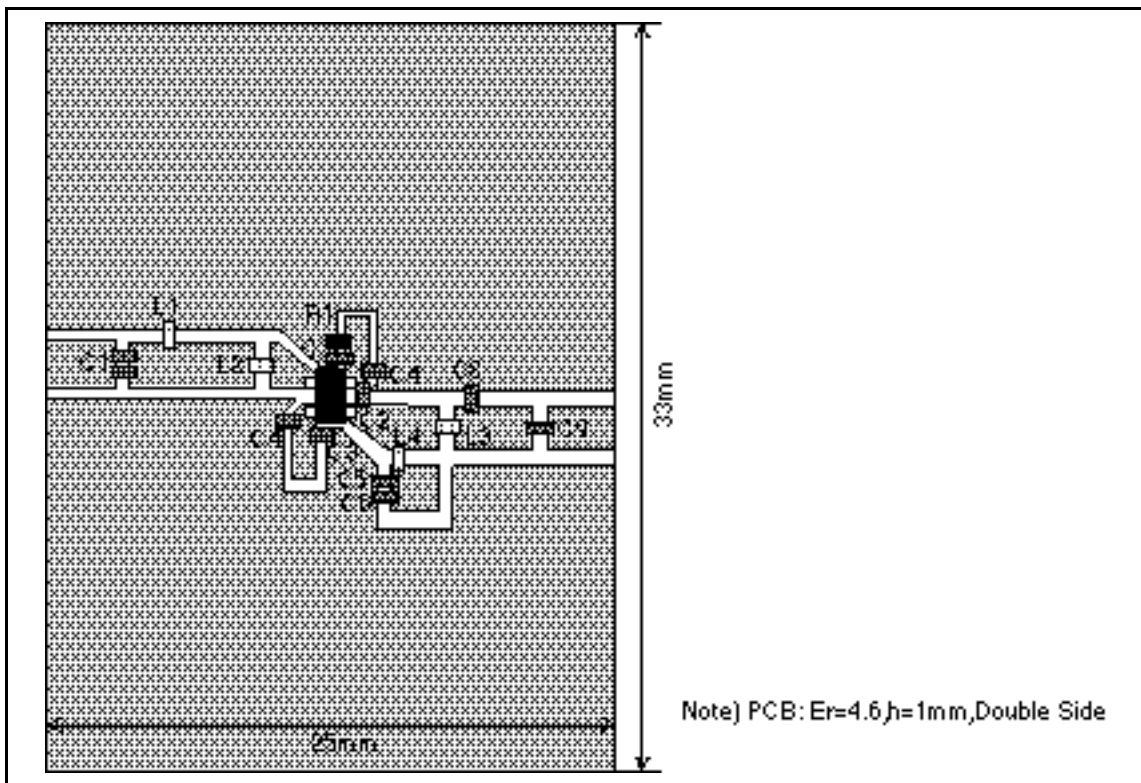
Characteristics (Test Fixture)



Application (f = 1.8 GHz LNA)

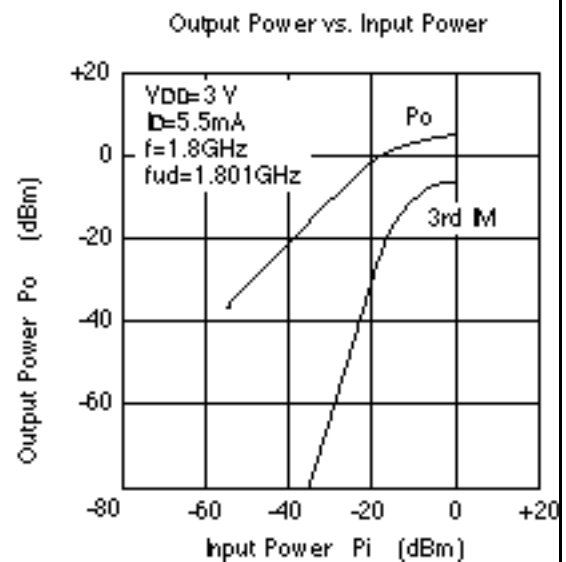
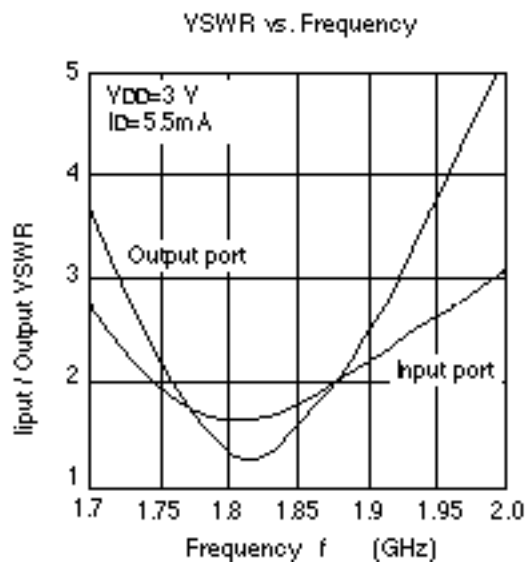
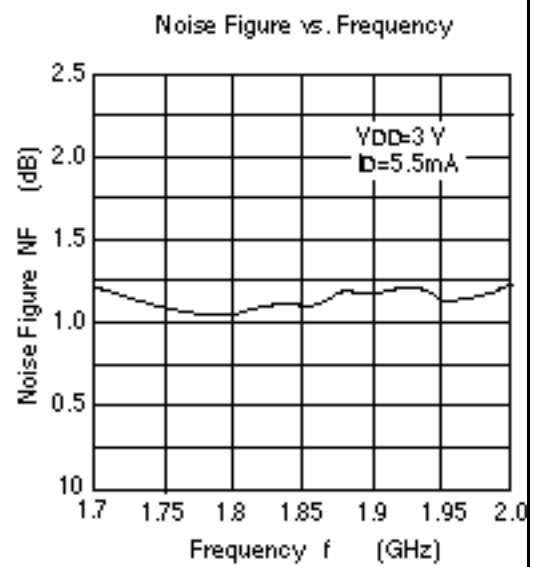
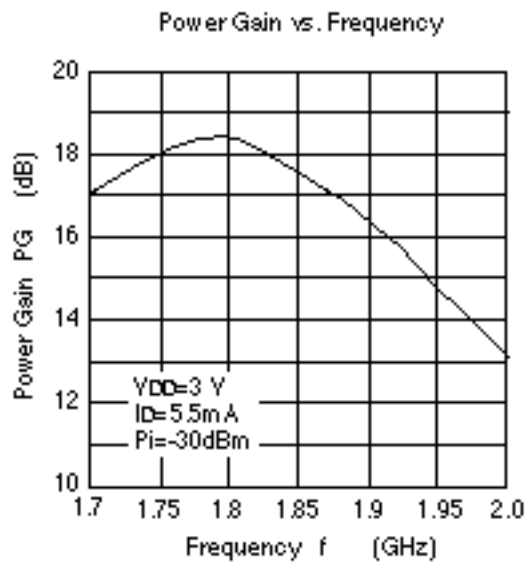


PCB Pattern & Parts Layouts



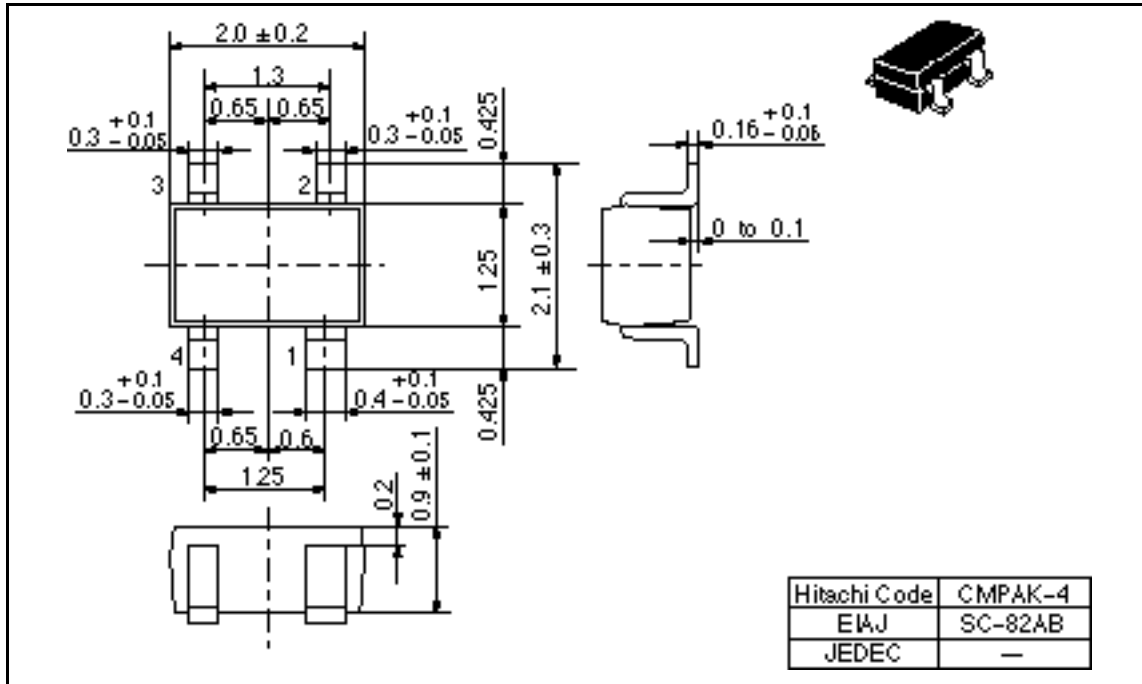
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Characteristics



Package Dimensions

Unit: mm



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HITACHI

Hitachi, Ltd.

Semiconductor & IC Div.

Nippon Bldg., 2-5-2, Ohite-machi, Chiyoda-ku, Tokyo 100, Japan

Tel: Tokyo (03) 3270-2111

Fax: (03) 3270-5109

For further information write to:

Hitachi Semiconductor
(America) Inc
2000 Sierra Point Parkway
Brisbane, CA. 94005-1897
U.S.A.
Tel: 800-285-1604
Fax: 303-297-0447

Hitachi Europe GmbH
Continental Europe
Danneberg Straße 3
D-85522 Feldkirchen
München
Tel: 089-9 94 80-0
Fax: 089-9 29 30-00

Hitachi Europe Ltd.
Electronic Components Div.
Northern Europe Headquarters
Whitebrook Park
Lower Cookham Road
Maidenhead
Berkshire SL6 8YA
United Kingdom
Tel: 01628-585000
Fax: 01628-585160

Hitachi Asia Pte. Ltd.
45 Collyer Quay #20-00
Hitachi Tower
Singapore 049318
Tel: 535-2100
Fax: 535-1533

Hitachi Asia (Hong Kong) Ltd.
Unit 705, North Tower,
World Finance Centre
Harbour City, Canton Road
Tsim Sha Tsui, Kowloon
Hong Kong
Tel: 27359218
Fax: 27308074

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